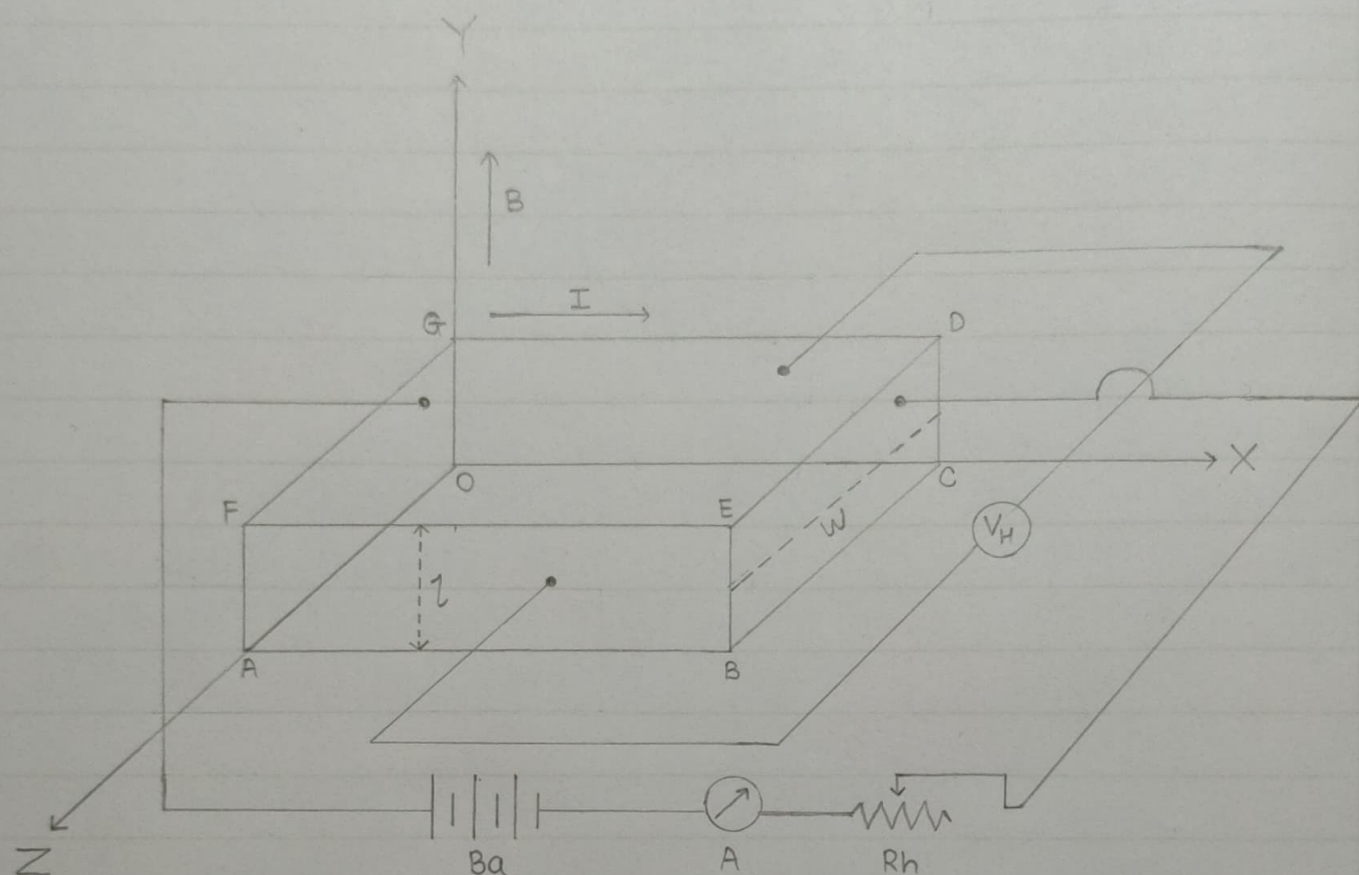


DIAGRAM  $\Rightarrow$



MEASUREMENT OF HALL COEFFICIENT  $\Rightarrow$

Current in the Hall effect setup = 2 mA.

Current in the constant current supply (A)	Magnetic Field (H) (gauss)	Hall Voltage ( $V_H$ ) (volts)	Hall Coefficient ( $R_H$ ) ( $\text{cm}^3 \text{C}^{-1}$ )
1.0	1320	12.5	$2.367 \times 10^4$
1.5	1940	18.1	$2.322 \times 10^4$
2.0	2620	23.2	$2.213 \times 10^4$
2.5	3040	27.4	$2.253 \times 10^4$

# DETERMINATION OF HALL - COEFFICIENT AND CARRIER TYPE FOR A SEMI - CONDUCTING MATERIAL.

AIM  $\Rightarrow$

To determine the hall coefficient of the given n-type or p-type semiconductor.

APPARATUS REQUIRED  $\Rightarrow$

Hall probe (n-type or p-type), Hall-effect setup, electromagnet, constant current power supply, gauss meter, etc.

FORMULAE  $\Rightarrow$

$$1) \text{ Hall coefficient } (R_H) = \frac{V_H \cdot t}{I_H} \times 10^8 \text{ cm}^3 \text{ C}^{-1}$$

where,  $V_H$  = Hall voltage (volt)  
 $t$  = Thickness of sample (cm)  
 $I$  = Current (ampere)  
 $H$  = Magnetic field (gauss)

$$2) \text{ Current Density } (n) = \frac{1}{R_H \cdot q} \text{ cm}^{-3}$$

where,  $R_H$  = Hall coefficient ( $\text{cm}^3 \text{ C}^{-1}$ )  
 $q$  = Charge of electron or hole (c)

$$3) \text{ Carrier Mobility } (\mu) = R_H \cdot \sigma \text{ cm}^2 \text{ V}^{-1} \text{ s}^{-1}$$

where,  $R_H$  = Hall coefficient ( $\text{cm}^3 \text{ C}^{-1}$ )  
 $\sigma$  = Conductivity ( $\text{C V}^{-1} \text{ s}^{-1} \text{ cm}^{-1}$ )



3.0	3600	31.2	$2.166 \times 10^4$
3.5	4390	35.6	$2.027 \times 10^4$
			MEAN $\Rightarrow 2.226 \times 10^4$

OBSERVATIONS  $\Rightarrow$

- 1> Thickness of the sample ( $t$ ) = 0.05 cms.
- 2> Resistivity of the sample ( $\rho$ ) =  $10 \text{ V C}^{-1} \text{ S cm}$ .
- 3> Conductivity of the sample ( $\sigma$ ) =  $0.1 \text{ C V}^{-1} \text{ S}^{-1} \text{ cm}^{-1}$ .
- 4> Charge of electron or hole ( $q$ ) =  $1.6 \times 10^{-19} \text{ C}$ .

CALCULATION  $\Rightarrow$

$$\begin{aligned}
 1> \quad R_H &= \frac{V_H \cdot t}{I_H} \times 10^8 \\
 &= \frac{12.5 \times 10^{-3} \times 0.05}{2 \times 10^{-3} \times 1320} \times 10^8 \\
 &= \frac{0.625}{2640} \times 10^8 = \frac{625}{2640} \times 10^5 = 0.2367 \times 10^5 \\
 &\approx 2.367 \times 10^4 \text{ cm}^3 \text{ C}^{-1}
 \end{aligned}$$

$$\begin{aligned}
 2> \quad R_H &= \frac{V_H \cdot t}{I_H} \times 10^8 \\
 &= \frac{18.1 \times 10^{-3} \times 0.05}{2 \times 10^{-3} \times 1940} \times 10^8 \\
 &= \frac{0.905}{3880} \times 10^8 = \frac{905}{3880} \times 10^5 = 0.2213 \times 10^5 \\
 &\approx 2.222 \times 10^4 \text{ cm}^3 \text{ C}^{-1}
 \end{aligned}$$

PRINCIPLE  $\Rightarrow$ 

HALL EFFECT : When a current carrying conductor is placed in a transverse magnetic field, a potential difference is developed across the conductor in a direction perpendicular to both the current and the magnetic field.

RESULT  $\Rightarrow$



$$\begin{aligned}
 3) \quad R_H &= \frac{V_H \cdot t}{IH} \times 10^8 \\
 &= \frac{23.2}{27.4} \times 10^{-8} \times 0.05 \times 10^8 \\
 &\quad 2 \times 10^{-8} \times 2620 \\
 &= \frac{1.16}{5240} \times 10^8 = \frac{1160}{5240} \times 10^5 = 0.2213 \times 10^5 \\
 &\approx 2.213 \times 10^4 \text{ cm}^3 \text{ C}^{-1}
 \end{aligned}$$

$$\begin{aligned}
 4) \quad R_H &= \frac{V_H \cdot t}{IH} \times 10^8 \\
 &= \frac{27.4 \times 10^{-8} \times 0.05}{2 \times 10^{-8} \times 3040} \times 10^8 \\
 &= \frac{1.37}{6080} \times 10^8 = \frac{1370}{6080} \times 10^5 = 0.2253 \times 10^5 \\
 &\approx 2.253 \times 10^4 \text{ cm}^3 \text{ C}^{-1}
 \end{aligned}$$

$$\begin{aligned}
 5) \quad R_H &= \frac{V_H \cdot t}{IH} \times 10^8 \\
 &= \frac{31.2 \times 10^{-8} \times 0.05}{2 \times 10^{-8} \times 3600} \times 10^8 \\
 &= \frac{1.56}{7200} \times 10^8 = \frac{1560}{7200} \times 10^5 = 0.2166 \times 10^5 \\
 &\approx 2.166 \times 10^4 \text{ cm}^3 \text{ C}^{-1}
 \end{aligned}$$

$$\begin{aligned}
 6) \quad R_H &= \frac{V_H \cdot t}{IH} \times 10^8 \\
 &= \frac{35.6 \times 10^{-8} \times 0.05}{2 \times 10^{-8} \times 4390} \times 10^8 \\
 &= \frac{1.78}{8780} \times 10^8 = \frac{1780}{8780} \times 10^5 = 0.2027 \times 10^5 \\
 &\approx 2.027 \times 10^4 \text{ cm}^3 \text{ C}^{-1}
 \end{aligned}$$

$$\text{Carrier Density } (n) = \frac{1}{R_H \cdot q} \text{ cm}^{-3}$$

$$\begin{aligned} \therefore n &= \frac{1}{2.226 \times 10^4 \times 1.6 \times 10^{-19}} = \frac{10^{19} \times 10^{-4}}{2.226 \times 1.6} \\ &= \frac{1}{3.5616} \times 10^{15} \approx 0.2807 \times 10^{15} \end{aligned}$$

$$\text{So, } n \approx 2.807 \times 10^{14} \text{ cm}^{-3}$$

$$\text{Carrier Mobility } (\mu) = R_H \cdot \sigma$$

$$\begin{aligned} \therefore \mu &= 2.226 \times 10^4 \times 0.1 \\ &\approx 2.226 \times 10^3 \text{ cm}^2 \text{ V}^{-1} \text{ s}^{-1} \end{aligned}$$



RESULT

- 1> The Hall coefficient of the given semi-conducting material =  $2.226 \times 10^4 \text{ cm}^3 \text{ C}^{-1}$ .
- 2> The carrier density =  $2.807 \times 10^{14} \text{ carriers/cm}^3$ .
- 3> The carrier mobility =  $2.226 \times 10^3 \text{ cm}^2/\text{volt} \cdot \text{sec}$